

1.Description

This Dual 30V N-channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

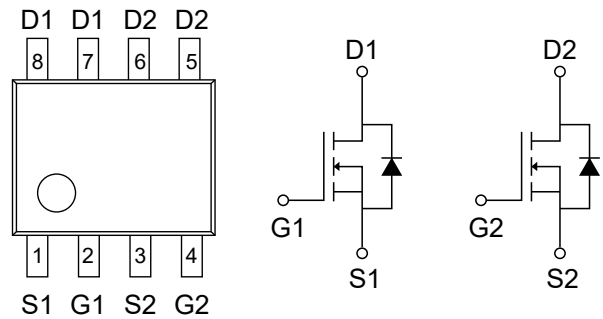
2.Features

- $V_{DS(V)}=30V$
- $I_D=7A$
- $R_{DS(ON)}<23m\Omega(V_{GS}=10V)$
- $R_{DS(ON)}<30m\Omega(V_{GS}=4.5V)$
- Low gate charge

3.Pinning information

Pin	Symbol	Description
2,4	G1,G2	GATE
1,3	S1,S2	SOURCE
5,6,7,8	D1,D2	DRAIN

SOP-8



4.Absolute Maximum Ratings $T_A=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Rating	Units
Drain to Source Voltage	V_{DS}	30	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current Continuous	I_D	7	A
Pulsed (Note 1a)		30	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	32	mJ
Power dissipation	P_D	1.6	W
Derate above $25^{\circ}C$		13	mW/ $^{\circ}C$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	$^{\circ}C$



5.Thermal Characteristics

Parameter	Symbol	Rating	Units
Thermal Resistance, Junction-to-Ambient (Note 1a)	$R_{\theta JA}$	78	°C/W
Thermal Resistance, Junction-to-Case (Note 1)	$R_{\theta JA}$	40	°C/W



6. Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

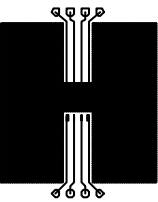
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	$I_D=250\mu\text{A}$ Referenced to 25°C		23		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$T_J=125^\circ\text{C}$			250	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$			± 100	nA
Gate to Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.2	1.7	2.5	V
Gate to Source Threshold Voltage Temperature Coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	$I_D=250\mu\text{A}$ Referenced to 25°C		-4.3		mV/ $^\circ\text{C}$
Drain to Source On Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=7\text{A}$		19	23	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=6\text{A}$		24	30	m Ω
Input Capacitance	C_{iss}	$V_{DS}=15\text{V}$		475	635	pF
Output Capacitance	C_{oss}	$V_{GS}=0\text{V}$		100	135	pF
Reverse Transfer Capacitance	C_{rss}	$f=1\text{MHz}$		65	100	pF
Gate Resistance	R_G	$f=1\text{MHz}$		0.9	1.6	Ω
Turn-On DelayTime	$t_{D(on)}$	$V_{DD}=15\text{V}$, $I_D=7\text{A}$ $V_{GS}=10\text{V}$, $R_{GS}=33\Omega$		5	10	ns
Rise Time	t_r			9	18	ns
Turn-Off DelayTime	$t_{D(off)}$			42	68	ns
Fall Time	t_f			21	34	ns
Total Gate Charge	Q_g	$V_{DS}=15\text{V}$, $I_D=7\text{A}$, $V_{GS}=10\text{V}$		9.2	13	nC
Total Gate Charge	Q_g	$V_{DS}=15\text{V}$, $I_D=7\text{A}$ $V_{GS}=5\text{V}$		5	7	nC
Gate to Source Gate Charge	Q_{gs}			1.5		nC
Gate to Drain "Miller" Charge	Q_{gd}			2		nC
Source to Drain Diode Voltage	V_{SD}	$I_{SD}=7\text{A}$		0.9	1.25	V
		$I_{SD}=2.1\text{A}$		0.8	1	V



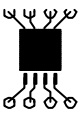
Diode Reverse Recovery Time	t_{rr}	$I_F=7A, dI_F/dt=100A/\mu s$			33	nS
Diode Reverse Recovery Charge	Q_{rr}				20	nC

Notes:

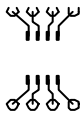
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when
mounted on a 0.5in²
pad of 2 oz copper.



b) 125° C/W when
mounted on a 0.02 in²
pad of oz. copper.



c) 135° C/W when
mounted on a minimum
pad.

Scale 1 : 1 on letter size paper

2: Starting $T_J=25^{\circ}C$, $L=1mH$, $I_{AS}=8A$, $V_{DD}=27V$, $V_{GS}=10V$.

3: Pulse Test:Pulse Width <300μs, Duty Cycle <2%.



7.1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

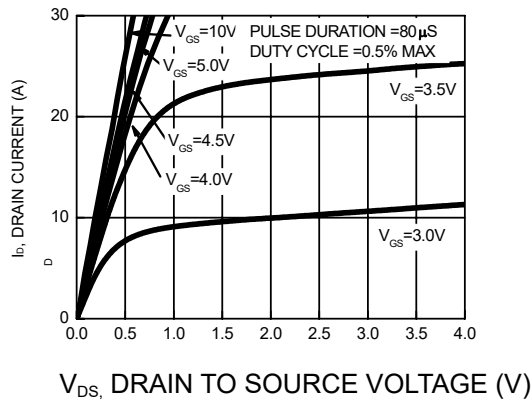


Figure 1: On-Region Characteristics.

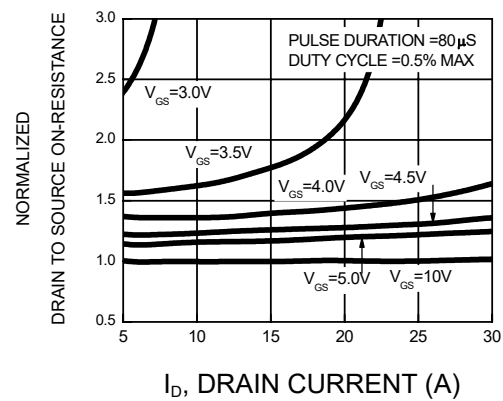


Figure 2: On-Resistance Variation with Drain Current and Gate Voltage.

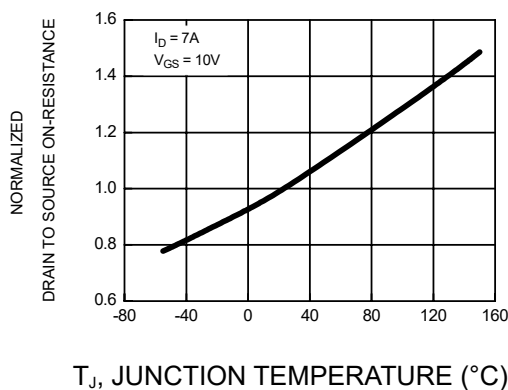


Figure 3: On-Resistance Variation with Temperature.

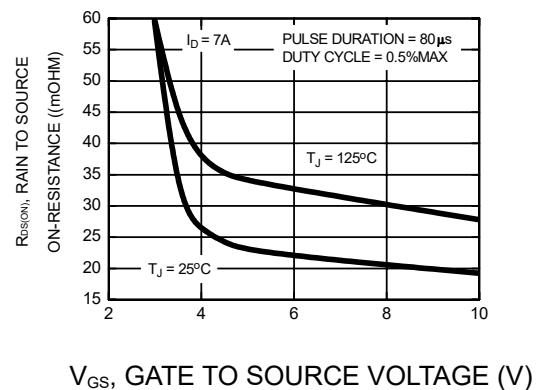


Figure 4: On-Resistance vs Gate to Source Voltage.

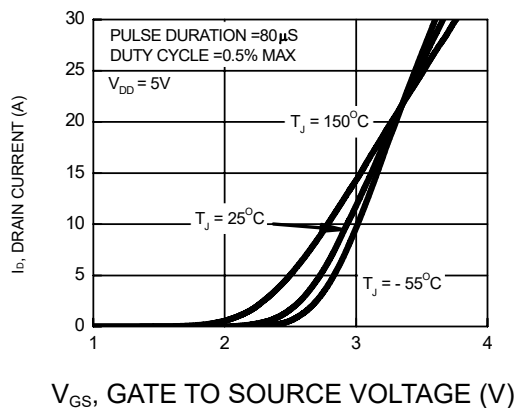


Figure 5: Transfer Characteristics.

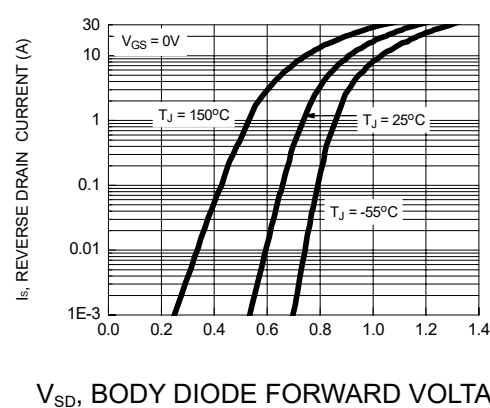


Figure 6: Source to Drain Diode Forward Voltage vs Source Current.



7.2 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

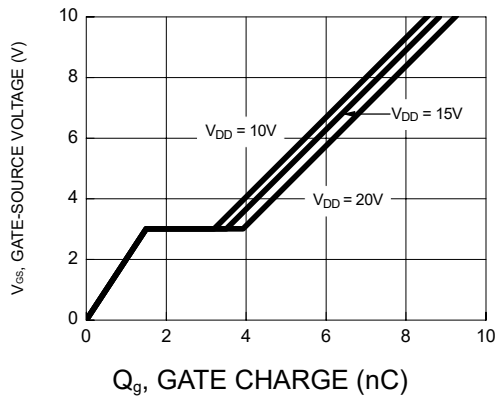


Figure 7: Gate-Charge Characteristics.

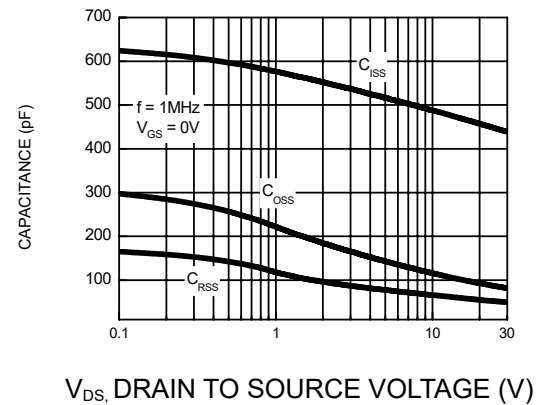


Figure 8: Capacitance vs Drain to Source Voltage.

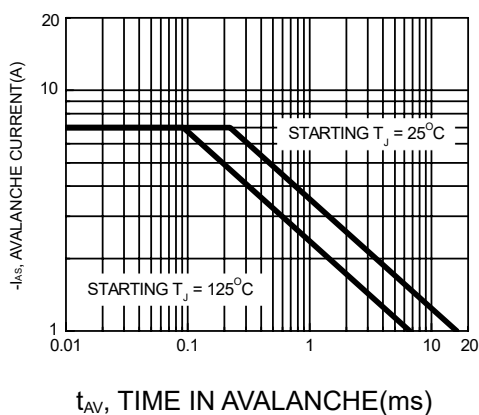


Figure 9: Unclamped Inductive Switching Capability.

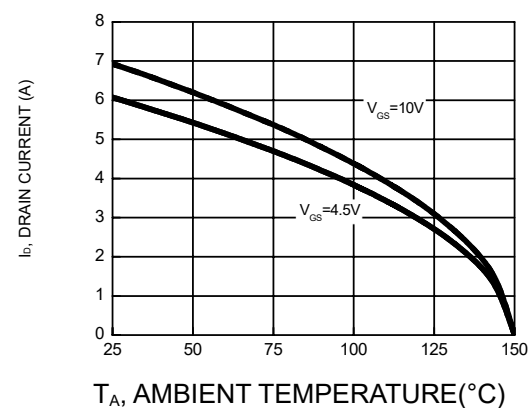


Figure 10: Maximum Continuous Drain Current vs Ambient Temperature.

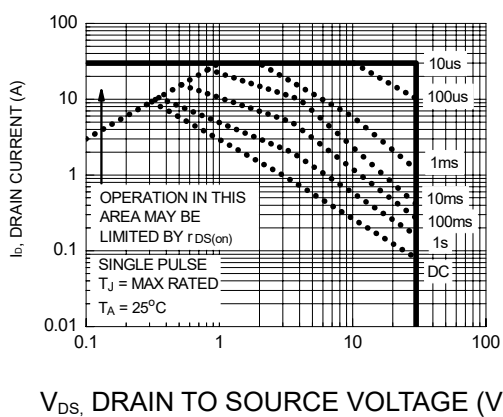


Figure 11: Forward Bias Safe Operating Area.

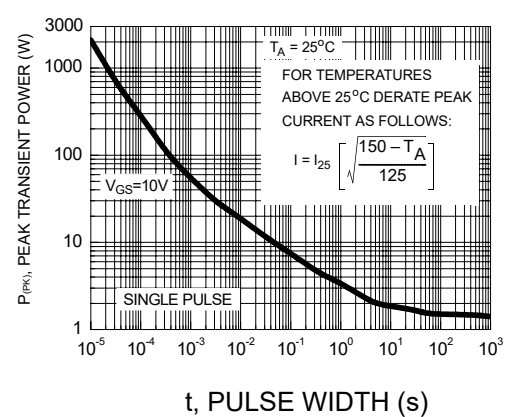
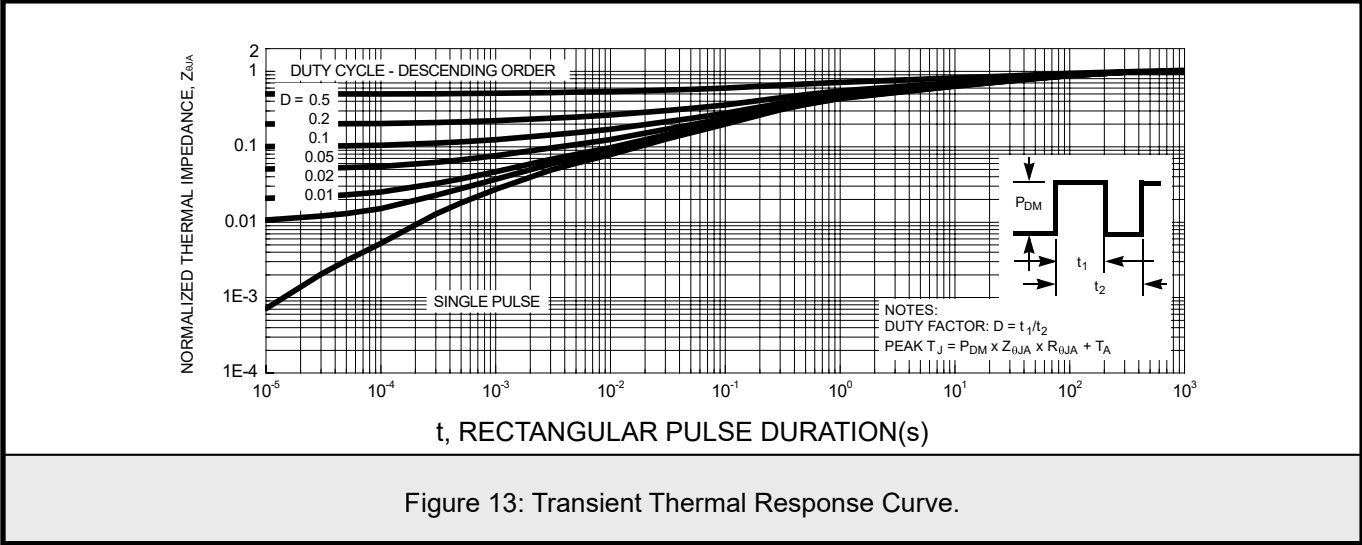


Figure 12: Single Pulse Maximum Power Dissipation.

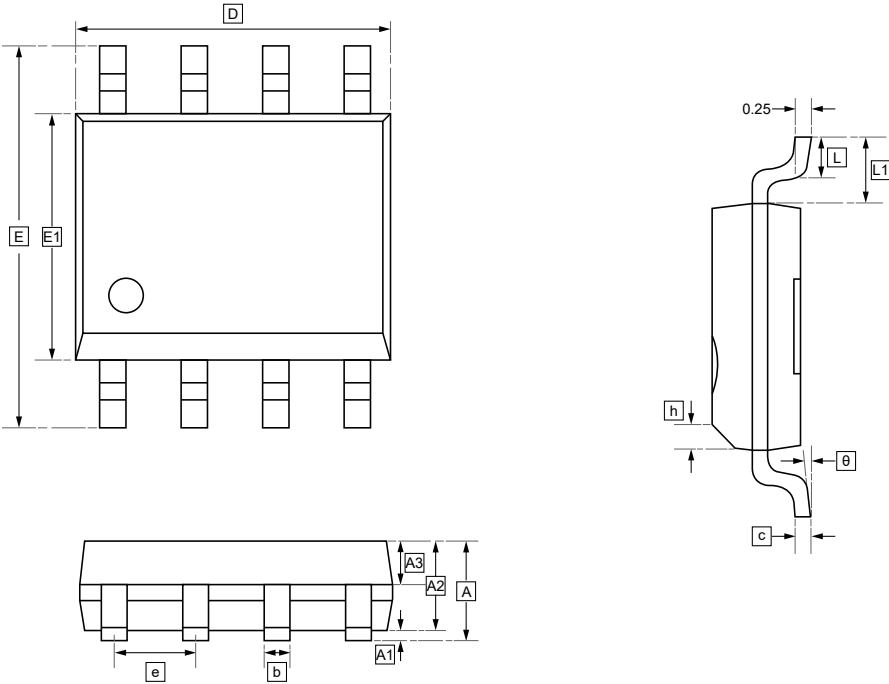


7.3Typical Characterisitics





8.SOP-8 Package Outline Dimensions



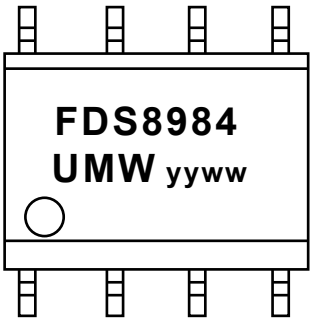
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	b	c	D	E	E1	e	h	L
Min	-	0.05	1.30	0.60	0.39	0.20	4.80	5.80	3.80	1.24	0.30	0.50
Max	1.75	0.20	1.50	0.70	0.47	0.24	5.00	6.20	4.00	1.30	0.50	0.80

Symbol	L1	θ
Min	1.00	0°
Max	1.10	8°



9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDS8984	SOP-8	3000	Tape and reel



10.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

When applying our products, please do not exceed the maximum rated values, as this may affect the reliability of the entire system. Under certain conditions, any semiconductor product may experience faults or failures. Buyers are responsible for adhering to safety standards and implementing safety measures during system design, prototyping, and manufacturing when using our products to prevent potential failure risks that could lead to personal injury or property damage.

Unless explicitly stated in writing, UMW products are not intended for use in medical, life-saving, or life-sustaining applications, nor for any other applications where product failure could result in personal injury or death. If customers use or sell the product for such applications without explicit authorization, they assume all associated risks.

When reselling, applying, or exporting, please comply with export control laws and regulations of China, the United States, the United Kingdom, the European Union, and other relevant countries, regions, and international organizations.

This document and any actions by UMW do not grant any intellectual property rights, whether express or implied, by estoppel or otherwise. The product names and marks mentioned herein may be trademarks of their respective owners.